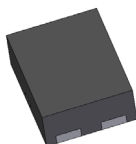
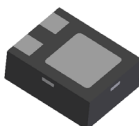


Features

- P-Channel MOSFET
- Very Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

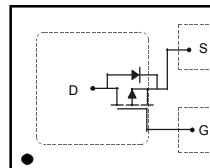


TOP VIEW



BOTTOM VIEW

DFN1411-3


TOP VIEW
Internal Schematic

Mechanical Data

- Case: DFN1411-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish - NiPdAu over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.003 grams (approximate)

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±12	V
Continuous Drain Current (Note 1)	I _D	-1.5 -1.2	A

T_A = 25°C
T_A = 70°C

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Power Dissipation (Note 1)	P _D	500	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	250	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0 -5.0	μA	T _J = 25°C T _J = 125°C V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	-0.45	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	92 134 180	150 200 240	mΩ	V _{GS} = -4.5V, I _D = -950mA
						V _{GS} = -2.5V, I _D = -670mA
						V _{GS} = -1.8V, I _D = -200mA
Forward Transconductance	g _{FS}	—	3.1	—	S	V _{DS} = -10V, I _D = -810mA
Diode Forward Voltage (Note 4)	V _{SD}	—	—	-0.9	V	V _{GS} = 0V, I _S = -360mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	320	—	pF	V _{DS} = -16V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	80	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	60	—	pF	

- Notes:
1. Device mounted on FR-4 PCB with 1 inch square pads.
 2. No purposefully added lead.
 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 4. Short duration pulse test used to minimize self-heating effect.

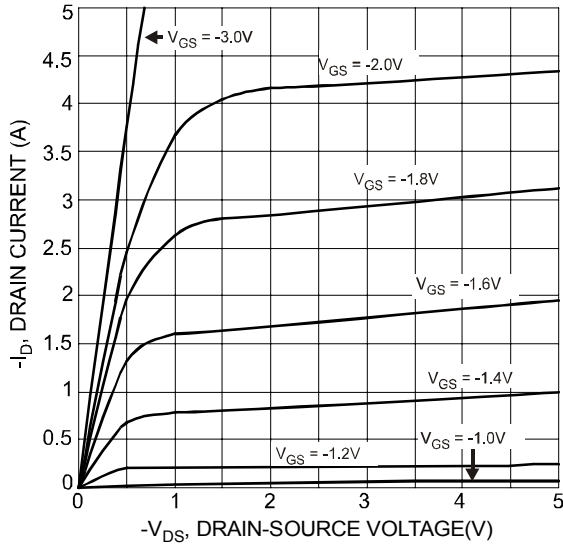


Fig. 1 Typical Output Characteristics

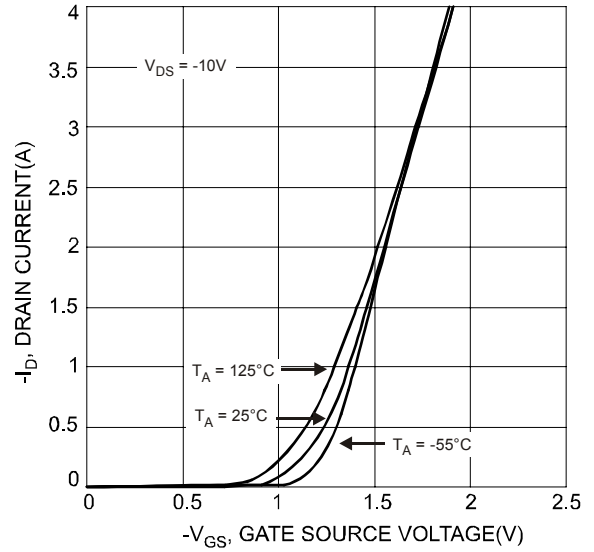


Fig. 2 Typical Transfer Characteristics

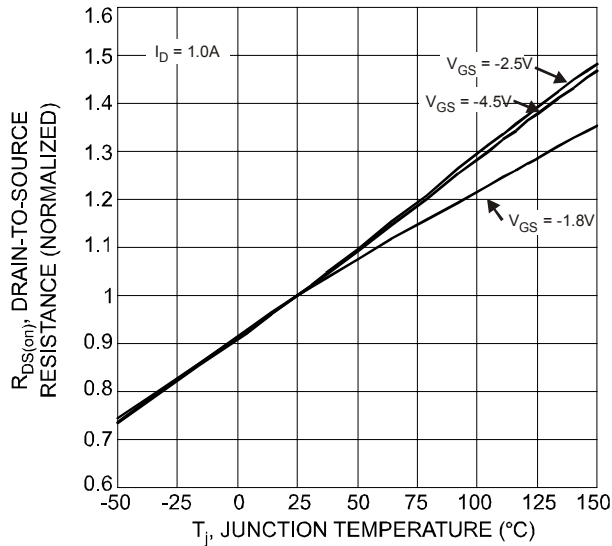


Fig. 3 On-Resistance Variation with Temperature

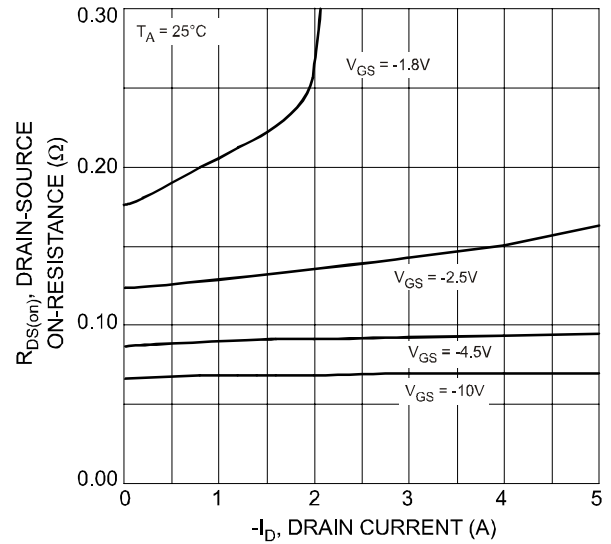


Fig. 4 On-Resistance vs. Drain Current and Gate Voltage

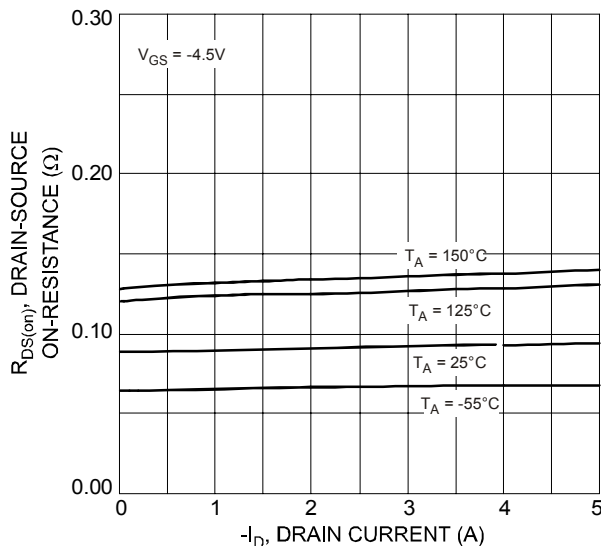


Fig. 5 Drain-Source On-Resistance vs. Drain Current and Temperature

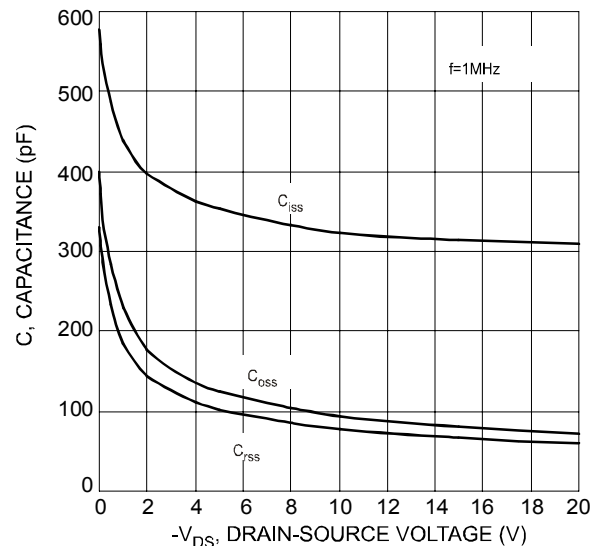


Fig. 6 Typical Capacitance

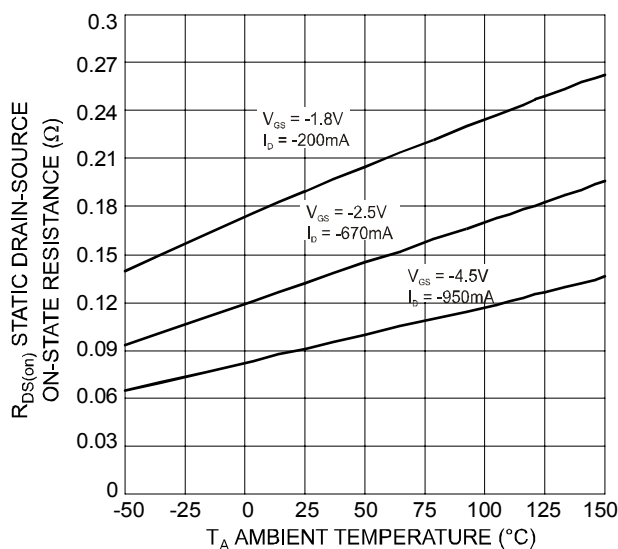


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

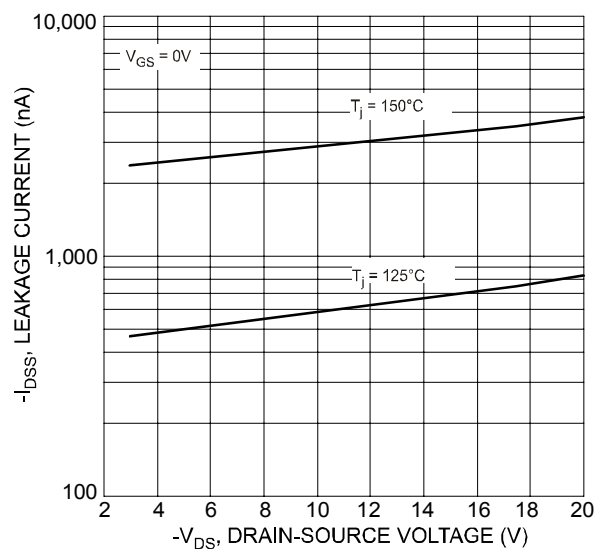


Fig. 8 Drain-Source Leakage Current vs. Voltage

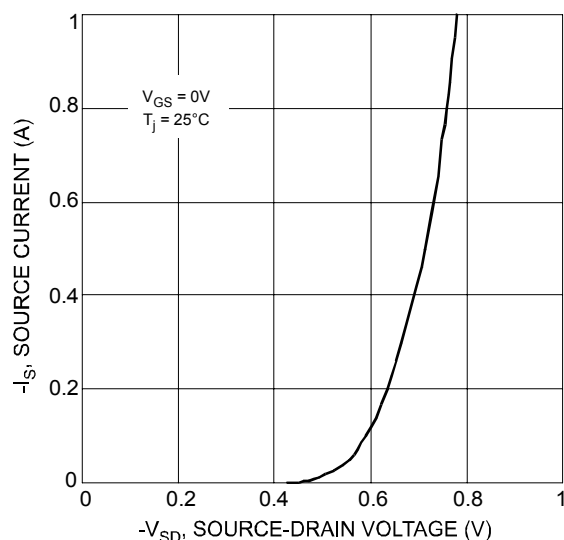


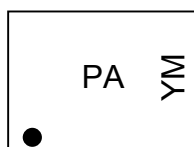
Fig. 9 Diode Forward Voltage vs. Current

Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2104LP-7	DFN1411-3	3000/Tape & Reel

 Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information

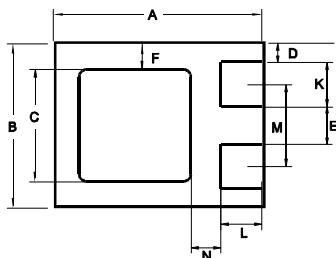
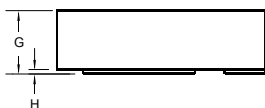

 PA = Marking Code
 YM = Date Code Marking
 Y = Year ex: U = 2007
 M = Month ex: 9 = September

Date Code Key

Year	2007	2008	2009	2010	2011	2012
Code	U	V	W	X	Y	Z

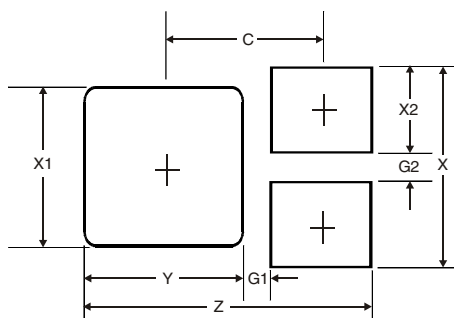
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



DFN1411-3			
Dim	Min	Max	Typ
A	1.35	1.48	1.40
B	1.05	1.18	1.10
C	0.65	0.85	0.75
D	—	—	0.125
E	—	—	0.25
F	—	—	0.175
G	0.47	0.53	0.50
H	0	0.05	0.02
K	0.25	0.35	0.30
L	0.22	0.33	0.275
M	—	—	0.55
N	—	—	0.20
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.38
G1	0.15
G2	0.15
X	0.95
X1	0.75
X2	0.40
Y	0.75
C	0.76

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<http://moschip.ru/get-element>

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